



2892

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

12/15 Supp. Amend

12-2302

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Filed: January 29, 2001  
Inventor(s):  
Halimaoui, Aomar

Examiner: Novacek, Christy L  
Group/Art Unit: 2822  
Atty. Dkt. No: 5310-03000

CERTIFICATE OF MAILING  
UNDER 37 C.F.R. §1.8  
DATE OF DEPOSIT: 12-4-02  
I hereby certify that this correspondence is being deposited with  
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Commissioner for Patents  
Washington, DC 20231  
*Jackie L. Pitre*  
Jackie L. Pitre

Title: PROCESS FOR FORMING  
AN OXIDE LAYER OF  
NON-UNIFORM  
THICKNESS ON THE  
SURFACE OF A SILICON  
SUBSTRATE

SUPPLEMENTAL AMENDMENT

Commissioner for Patents  
Washington, D.C. 20231

Amendment

Sir:

Please amend the above-captioned application as follows:

*In the Claims:*

Please amend the claims as follows:

33. (Amended) A process for forming a semiconductor device comprising a plurality  
of MOS transistors at predetermined regions of a silicon substrate, comprising: